

Silicon NPN transistor epitaxial type C5932

[Applications]

Inverter circuit of CCFL

[Feature]

High voltage VCEO= 200V

Collector current IC= 1A

Low collector saturation voltage VCE(sat)= 0.25V (Max.) at IC= 500mA, IB= 25mA

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	300	V
Collector-emitter voltage	VCEO	200	V
Emitter-base voltage	VEBO	6	V
Collector current	IC	1	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	300	-	-	V	IC= 100uA
Collector-emitter breakdown voltage	BVCEO	200	-	-	V	IC= 1mA
Emitter-base breakdown voltage	BVEBO	6	-	-	V	IE= 100uA
Collector cut-off current	ICBO	-	-	1	uA	VCB= 300V
Collector cut-off current	ICES	-	-	1	uA	VCES= 300V
Emitter cut-off current	IEBO	-	-	1	uA	VEB= 6V
DC current gain 1	hFE 1	140	-	-	-	VCE= 5V, IC= 50mA
DC current gain 2	hFE 2	140	-	340	-	VCE= 5V, IC= 200mA
DC current gain 3	hFE 3	10	-	-	-	VCE= 5V, IC= 1A
Collector-emitter saturation voltage	VCE(sat)	-	-	0.25	V	IC= 500mA, IB= 25mA
Base-emitter saturation voltage	VBE(sat)	-	-	1	V	IC= 500mA, IB= 25mA
Base-emitter on voltage	VBE(on)	0.45	-	0.8	V	VCE= 5V, IC= 5mA
Transition frequency	fT	20	50	-	MHz	VCE= 5V, IE=-200mA
Collector output capacitance	Cob	-	-	20	pF	VCB= 10V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

No. C5932-20070213

Fig.1 IC - VBE(on)
at VCE= 5V, Ta= 25C

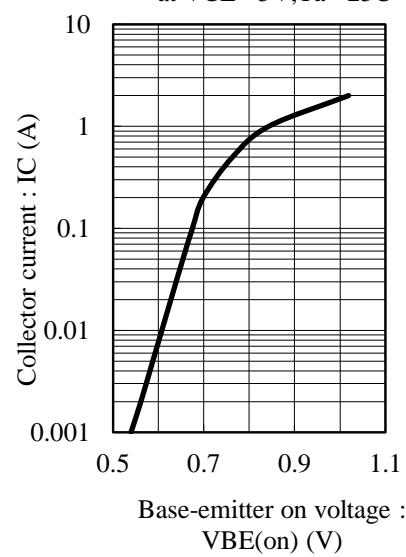


Fig.2 hFE - IC
at VCE= 5V, Ta= 25C

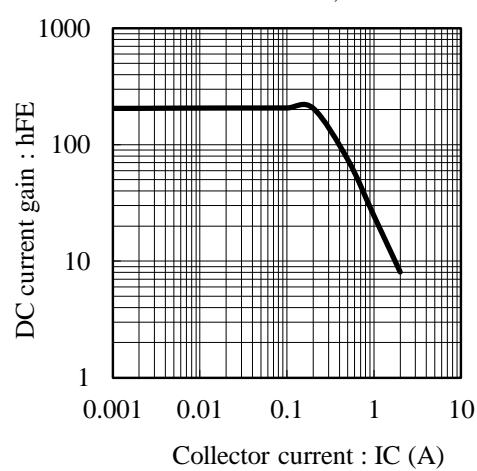


Fig.3 VCE(sat) - IC
at IC/IB= 20, Ta= 25C

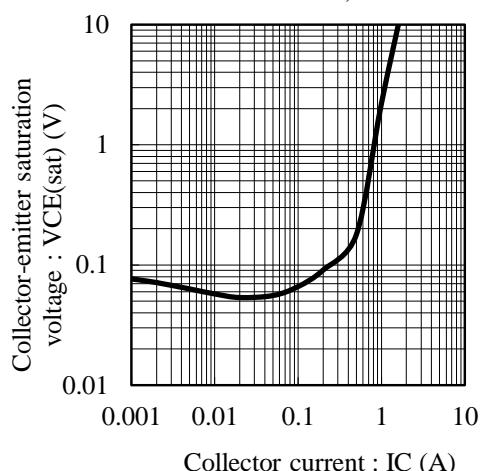


Fig.4 VBE(sat) - IC
at IC/IB= 20, Ta= 25C

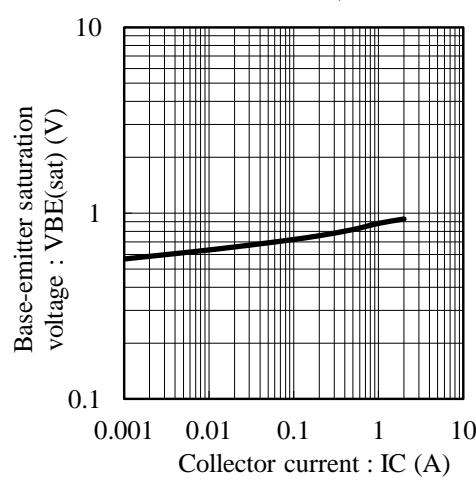


Fig.5 fT - IE
at VCE= 5V, Ta= 25C

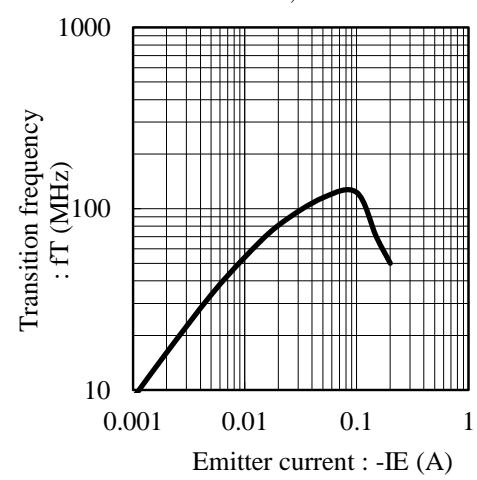


Fig.6 Cob - VCB
at f= 1MHz, Ta= 25C

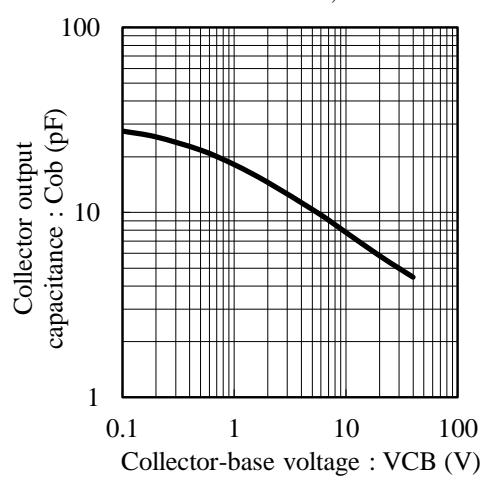


Fig.7 Cib - VEB
at f= 1MHz, Ta= 25C

